

# **HAT2179R**

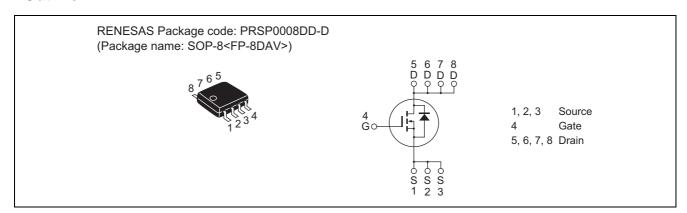
# Silicon N Channel MOS FET High Speed Power Switching

REJ03G1570-0200 Rev.2.00 Jul 17, 2009

#### **Features**

- Low on-resistance
- Low drive current
- High density mounting

## **Outline**



# **Absolute Maximum Ratings**

 $(Ta = 25^{\circ}C)$ 

Item	Symbol	Ratings	Unit
Drain to source voltage	V <sub>DSS</sub>	600	V
Gate to source voltage	V <sub>GSS</sub>	±30	V
Drain current	I <sub>D</sub>	0.7	А
Drain peak current	I <sub>D (pulse)</sub> Note1	2.0	А
Body-drain diode reverse drain current	I <sub>DR</sub>	0.7	А
Body-drain diode reverse drain peak current	I <sub>DR (pulse)</sub> Note1	2.0	А
Channel dissipation	Pch Note2	2.5	W
Channel temperature	Tch	150	°C
Storage temperature	Tstg	−55 to +150	°C

Notes: 1.  $PW \le 10 \mu s$ , duty cycle  $\le 1\%$ 

2. When using the glass epoxy board (FR4 40 x 40 x 1.6 mm), PW  $\leq$  10 s

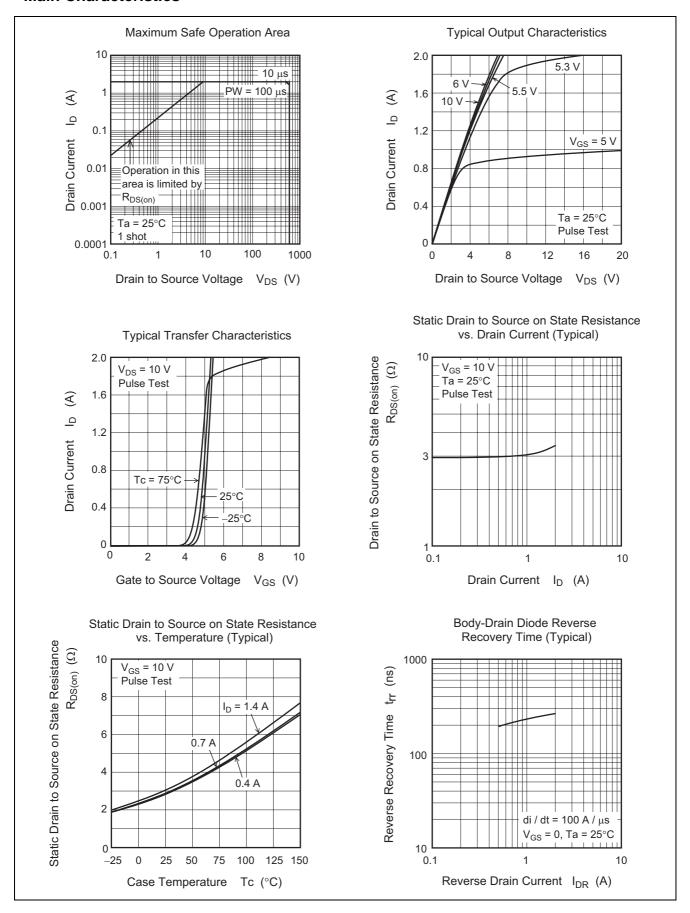
# **Electrical Characteristics**

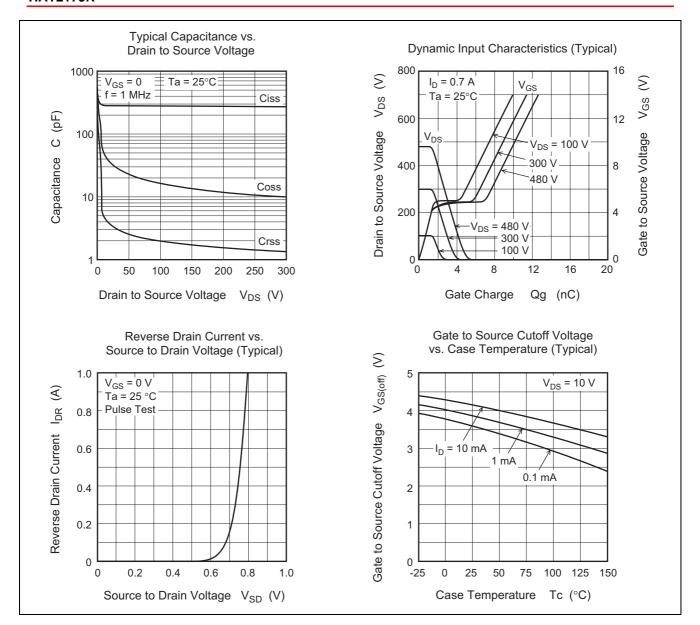
 $(Ta = 25^{\circ}C)$ 

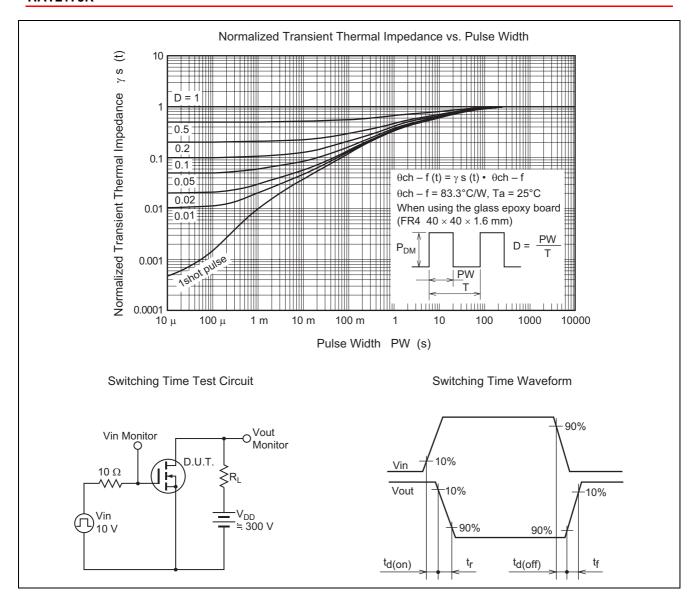
Item	Symbol	Min	Тур	Max	Unit	Test conditions
Drain to source breakdown voltage	$V_{(BR)DSS}$	600	_	_	V	$I_D = 10 \text{ mA}, V_{GS} = 0$
Zero gate voltage drain current	I <sub>DSS</sub>	_	_	1	μΑ	$V_{DS} = 600 \text{ V}, V_{GS} = 0$
Gate to source leak current	I <sub>GSS</sub>	1	_	±0.1	μΑ	$V_{GS} = \pm 30 \text{ V}, V_{DS} = 0$
Gate to source cutoff voltage	$V_{GS(off)}$	3.0	_	5.0	V	$V_{DS} = 10 \text{ V}, I_D = 1 \text{ mA}$
Forward transfer admittance	yfs	0.8	1.2	_	S	$I_D = 0.4 \text{ A}, V_{DS} = 10 \text{ V}^{\text{Note3}}$
Static drain to source on state	R <sub>DS(on)</sub>	_	3.5	4.5	Ω	$I_D = 0.4 \text{ A}, V_{GS} = 10 \text{ V}^{\text{Note3}}$
resistance						
Input capacitance	Ciss		280	_	pF	V <sub>DS</sub> = 25 V
Output capacitance	Coss		31	_	pF	V <sub>GS</sub> = 0 f = 1 MHz
Reverse transfer capacitance	Crss		3.8	_	pF	
Turn-on delay time	t <sub>d(on)</sub>	_	24	_	ns	I <sub>D</sub> = 0.4 A
Rise time	t <sub>r</sub>	_	15	_	ns	V <sub>GS</sub> = 10 V
Turn-off delay time	t <sub>d(off)</sub>	_	50	_	ns	$R_L = 750 \Omega$
Fall time	t <sub>f</sub>	_	58	_	ns	$Rg = 10 \Omega$
Total gate charge	Qg	_	10	_	nC	V <sub>DD</sub> = 480 V
Gate to source charge	Qgs	_	1.6	_	nC	V <sub>GS</sub> = 10 V
Gate to drain charge	Qgd	_	5.4	_	nC	$I_D = 0.7 A$
Body-drain diode forward voltage	$V_{DF}$	_	0.8	1.2	V	$I_F = 0.7 \text{ A}, V_{GS} = 0^{\text{Note3}}$
Body-drain diode reverse	t <sub>rr</sub>	_	200	_	ns	$I_F = 0.7 \text{ A}, V_{GS} = 0$
recovery time						$di_F/dt = 100 A/\mu s$

Notes: 3. Pulse test

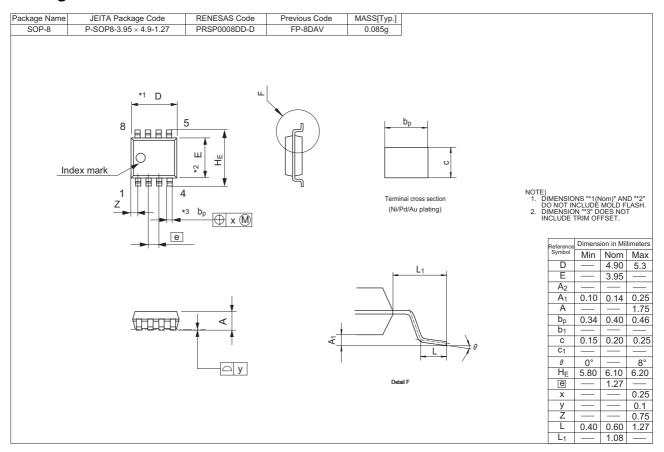
### **Main Characteristics**







## **Package Dimensions**



# **Ordering Information**

Part No.	Quantity	Shipping Container
HAT2179R-EL-E	2500 pcs	Taping

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